



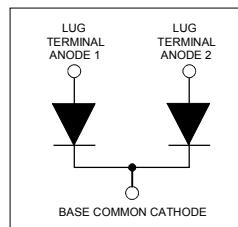
S1242

HEXFRED™

Ultrafast, Soft Recovery Diode

Features

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 400V$
$V_F(\text{typ.})^{\circledcirc} = 1V$
$I_F(\text{AV}) = 320A$
$Q_{rr} (\text{typ.}) = 420\text{nC}$
$I_{RRM}(\text{typ.}) = 8.7A$
$t_{rr}(\text{typ.}) = 45\text{ns}$
$dI_{(rec)M}/dt (\text{typ.})^{\circledcirc} = 280A/\mu\text{s}$

Description/Applications

HEXFRED™ diodes are optimized to reduce losses and EMI/ RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

Absolute Maximum Ratings

Parameters	Max	Units
V_R Cathode-to-Anode Voltage	400	V
$I_F @ T_C = 25^\circ\text{C}$ Continuous Forward Current	321	A
$I_F @ T_C = 100^\circ\text{C}$ Continuous Forward Current	160	
I_{FSM} Single Pulse Forward Current ①	1200	
E_{AS} Non-Repetitive Avalanche Energy ②	1.4	mJ
$P_D @ T_C = 25^\circ\text{C}$ Maximum Power Dissipation	625	W
$P_D @ T_C = 100^\circ\text{C}$ Maximum Power Dissipation	250	
T_J, T_{STG} Operating Junction and Storage Temperature Range	- 55 to 150	°C

Case Styles

S1242



TO-244

- ① Limited by junction temperature
 ② $L = 100\mu\text{H}$, duty cycle limited by max T_J
 ③ 125°C

Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage,	400	-	-	V	$I_R = 100\mu\text{A}$
V_{FM}	Max. Forward Voltage	-	1.10	1.35	V	$I_F = 160\text{A}$
		-	1.30	1.55	V	$I_F = 320\text{A}$
		-	1.00	1.20	V	$I_F = 160\text{A}, T_J = 125^\circ\text{C}$
I_{RM}	Max. Reverse Leakage Current	-	2.0	12	μA	$V_R = V_R$ Rated
		-	3.0	16	mA	$T_J = 125^\circ\text{C}, V_R = 320\text{V}$
C_T	Junction Capacitance	-	370	500	pF	$V_R = 200\text{V}$
L_S	Series Inductance	-	5.0	-	nH	From top of terminal hole,to mounting plane

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
t_{rr}	Reverse Recovery Time	-	45	-	ns	$I_F = 1.0\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$
t_{rr1}		-	90	140		$T_J = 25^\circ\text{C}$
t_{rr2}		-	290	440		$T_J = 125^\circ\text{C}$
I_{RRM1}	Peak Recovery Current	-	8.7	20	A	$T_J = 25^\circ\text{C}$
I_{RRM2}		-	18	30		$T_J = 125^\circ\text{C}$
Q_{rr1}	Reverse Recovery Charge	-	420	1100	nC	$T_J = 25^\circ\text{C}$
Q_{rr2}		-	2600	7000		$T_J = 125^\circ\text{C}$
$dI_{(rec)M}/dt_1$	$dI_{(rec)M}/dt_1$	-	300	-	A/ μs	$T_J = 25^\circ\text{C}$
$dI_{(rec)M}/dt_2$		-	280	-		$T_J = 25^\circ\text{C}$

Thermal - Mechanical Characteristics

Parameters		Min	Typ	Max	Units
T_J	Max. Junction Temperature Range	-	-	-55 to 150	°C
T_{Stg}	Max. Storage Temperature Range	-	-	-55 to 150	
R_{thJC}	Thermal Resistance, Junction to Case Per Leg	-	-	0.24	°C/W
	Thermal Resistance, Junction to Case Per Module	-	-	0.12	
R_{thCS}	Thermal Resistance, Case to Heatsink	-	0.10	-	
Wt	Weight	-	68 (2.4)	-	g (oz)
Mounting Torque (*)		30 (3.4)	-	40 (4.6)	lbf.in (N.m)
Mounting Torque Center Hole		12 (1.4)	-	18 (2.1)	
Terminal Torque		30 (3.4)	-	40 (4.6)	
Vertical Pull		-	-	80	lbf.in
2 inch Lever Pull		-	-	35	

(*) Mounting surface must be smooth, flat, free or burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5-10lbf.in steps until desired or maximum torque limits are reached

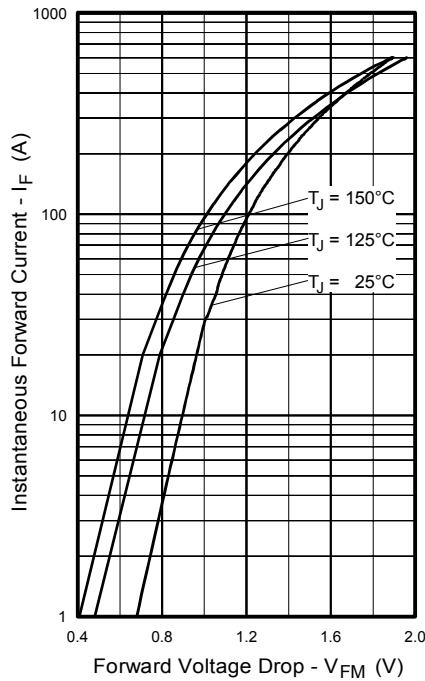


Fig. 1 - Maximum Forward Voltage Drop
vs. Instantaneous Forward Current (per Leg)

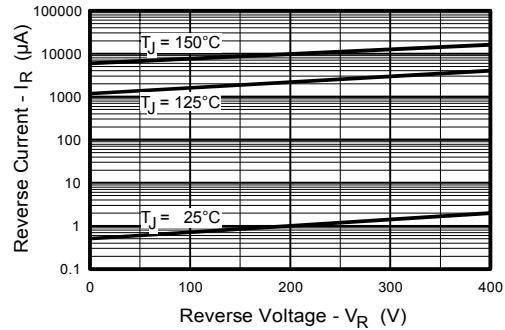


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

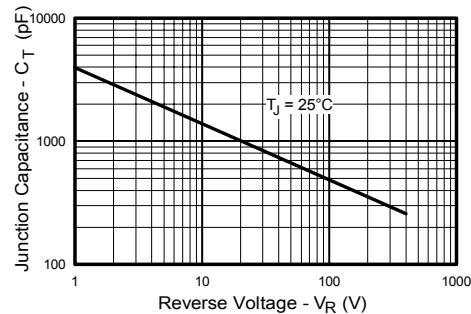


Fig. 3 - Typical Junction Capacitance vs.
Reverse Voltage, (per Leg)

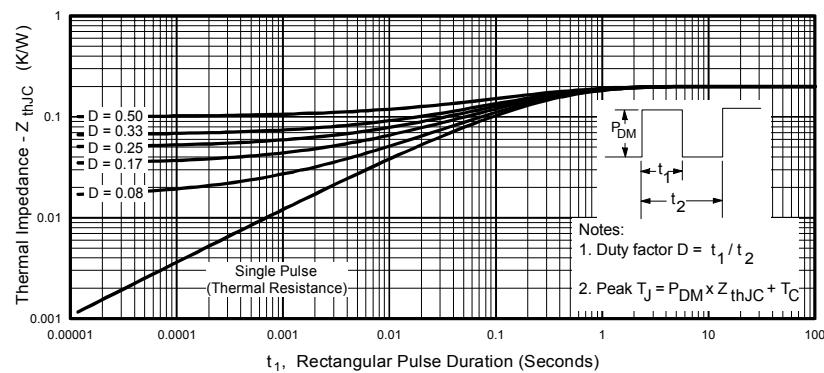


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics, (per Leg)

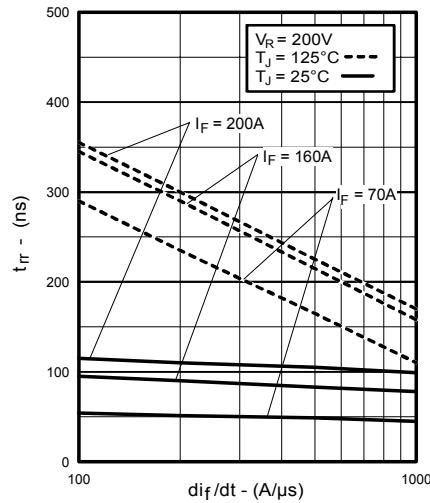


Fig. 5 - Typical Reverse Recovery vs. di_F/dt ,
(per Leg)

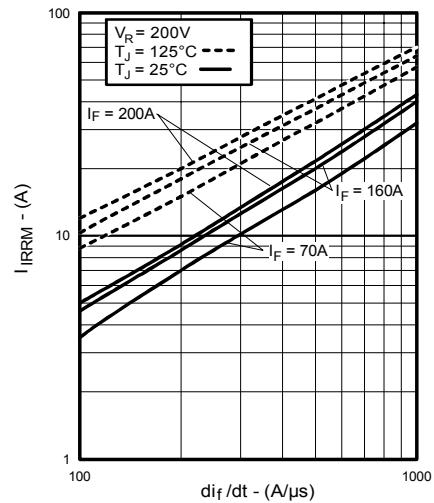


Fig. 6 - Typical Recovery Current vs. di_F/dt ,
(per Leg)

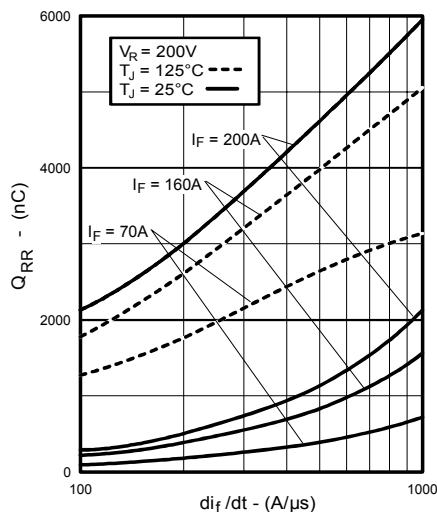


Fig. 7 - Typical Stored Charge vs. di_F/dt ,
(per Leg)

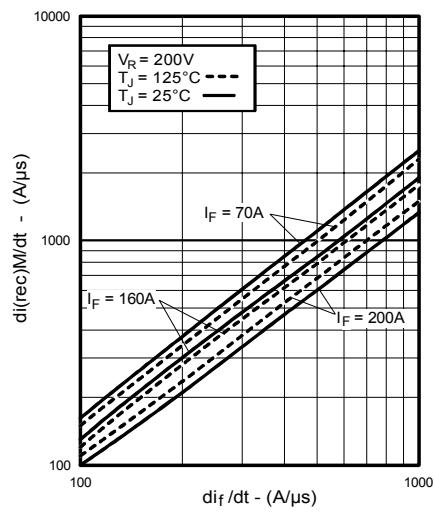


Fig. 8 - Typical $dI_{(rec)}/dt$ vs. di_F/dt ,
(per Leg)

Reverse Recovery Circuit

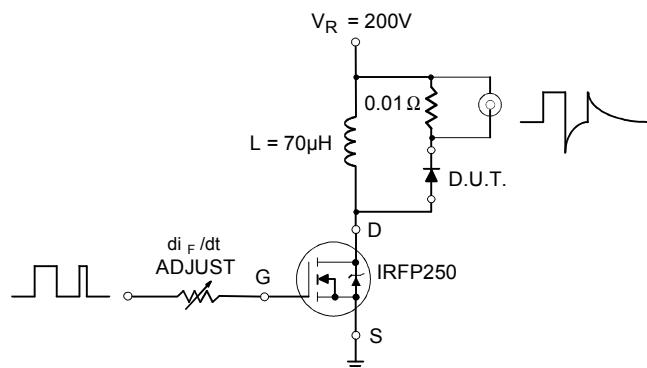
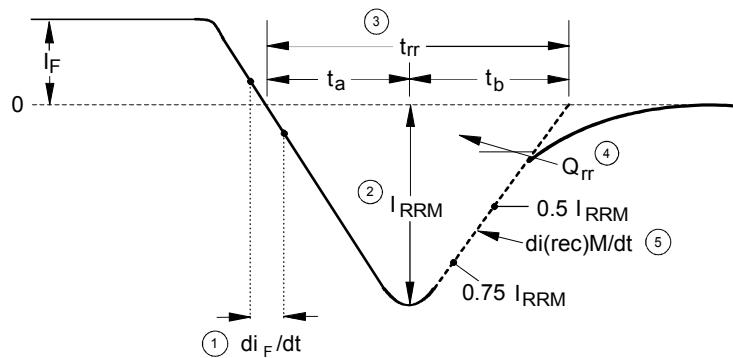


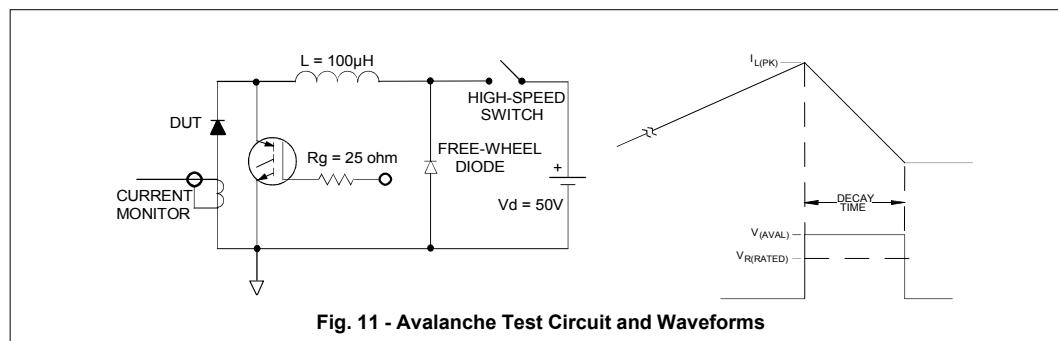
Fig. 9- Reverse Recovery Parameter Test Circuit



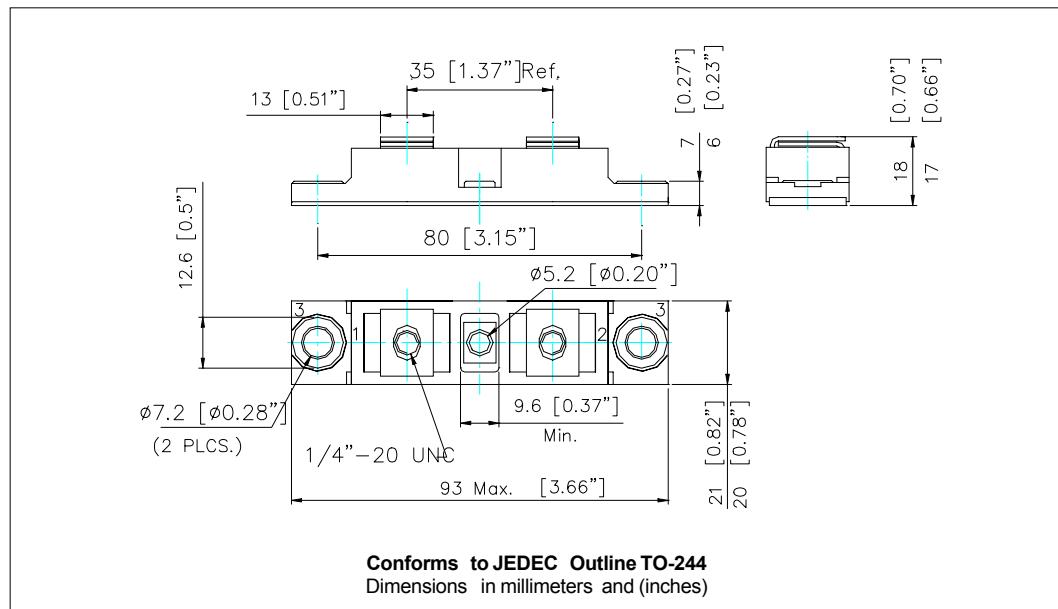
1. di_F/dt - Rate of change of current through zero crossing
2. I_{RRM} - Peak reverse recovery current
3. t_{rr} - Reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current
4. Q_{rr} - Area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$
5. $di(\text{rec}) M / dt$ - Peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



Outline Table



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
 Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7309
 Visit us at www.irf.com for sales contact information. 02/01